

## **INCHANGE SEMICONDUCTOR**

## **isc Silicon PNP Power Transistor**

# BD746/A/B/C

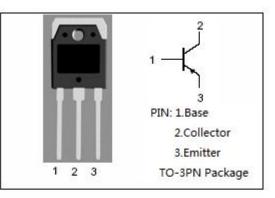
### DESCRIPTION

- Collector Current -I<sub>C</sub>= -20A
- Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub> = -45V(Min)- BD746; -60V(Min)- BD746A -80V(Min)- BD746B; -100V(Min)- BD746C
- Complement to Type BD745/A/B/C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

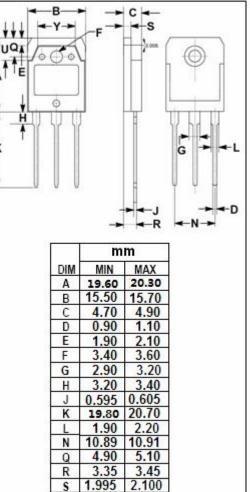
#### **APPLICATIONS**

• Designed for use in general purpose power amplifier and switching applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)



SYMBOL	PARAMETER		VALUE	UNIT	
Vcer	Collector-Emitter Voltage (R <sub>BE</sub> = 100 Ω )	BD746	-50		
		BD746A	-70	v	
		BD746B	-90		
		BD746C	-110		
V <sub>CEO</sub>	Collector-Emitter Voltage	BD746	-45	V	
		BD746A	-60		
		BD746B	-80		
		BD746C	-100		
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V		
lc	Collector Current-Continu	-20	A		
I <sub>CM</sub>	Collector Current-Peak	-25	A		
I <sub>B</sub>	Base Current	-7	А		
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃		3.5	W	
	Collector Power Dissipation @ $T_c=25^{\circ}C$		115		
TJ	Junction Temperature	150	°C		
T <sub>stg</sub>	Storage Temperature Ra	-65~150	°C		



isc website: www.iscsemi.cn

<sup>1</sup> *isc & iscsemi* is registered trademark

H

5.90

9.90

6.20

10.10



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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	SYMBOL PARAMETER		CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	BD746		-45			V
		BD746A	– − I <sub>C</sub> = -30mA ;I <sub>B</sub> =0	-60			
		BD746B		-80			
		BD746C		-100			
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -20A; I <sub>B</sub> = -5A			-3.0	V
V <sub>BE(on)-1</sub>	Base-Emitter On Voltage		I <sub>C</sub> = -5A; V <sub>CE</sub> = -4V			-1.0	V
V <sub>BE(on)-2</sub>	Base-Emitter On Voltage		Ic= -20A; Vce= -4V			-3.0	V
ICES	Collector Cutoff Current	BD746	$V_{CE}$ = -50V; $V_{BE}$ = 0 $V_{CE}$ = -50V; $V_{BE}$ = 0; $T_{C}$ = 125°C			-0.1 -5.0	
		BD746A	V <sub>CE</sub> = -70V; V <sub>BE</sub> = 0 V <sub>CE</sub> = -70V; V <sub>BE</sub> = 0; T <sub>C</sub> = 125℃		-0.1 -5.0	mA	
		BD746B	V <sub>CE</sub> = -90V; V <sub>BE</sub> = 0 V <sub>CE</sub> = -90V; V <sub>BE</sub> = 0; T <sub>C</sub> = 125℃				-0.1 -5.0
		BD746C	V <sub>CE</sub> = -110V; V <sub>BE</sub> = 0 V <sub>CE</sub> = -110V; V <sub>BE</sub> = 0; T <sub>C</sub> = 125℃			-0.1 -5.0	
I <sub>CEO</sub>	Collector Cutoff Current	BD746/A	V <sub>CE</sub> = -30V; I <sub>B</sub> = 0				
		BD746B/C	V <sub>CE</sub> = -60V; I <sub>B</sub> = 0			-0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current		V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-0.5	mA
h <sub>FE-1</sub>	DC Current Gain		I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V	40			
h <sub>FE-2</sub>	DC Current Gain		I <sub>C</sub> = -5A; V <sub>CE</sub> = -4V	20		150	
h <sub>FE-3</sub>	DC Current Gain		I <sub>C</sub> = -20A; V <sub>CE</sub> = -4V	5			

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